

## **Alessandro Cataldo**

#### **ABOUT ME**

I am a recently graduated **master student** in **Materials Engineering and Nanotechnology** in **Politecnico di Milano** looking forward to a **new challenge**. During my master thesis at Consiglio Nazionale delle Ricerche - Institute for Microelectronics and Microsystems, I worked on 2D materials, focusing on the growth of MoS<sub>2</sub> and its Raman characterization, matching my personal and academic interest in electronics. I am very **proactive**, **ambitious**, **indipendent** and **organised** and I am searching for new opportunities to learn and apply my skills.

#### **WORK EXPERIENCE**

#### Stage

Consiglio Nazionale delle Ricerche - Institute for Microelectronics and Microsystems [ 2022 – 2023 ]

Effects of precursor chemistry in few-layers  $MoS_2$  from AP-CVD sulphurisation. The work focused on reporting a method for the synthesis of large-area ( $\sim cm^2$ ) few-layers  $MoS_2$  via liquid precursor CVD, where the ammonium heptamolybdate (AHM) Mo precursor is provided via solution spin-coating. In particular, we focused on the effect of different inorganic seed promoters (NaOH, KCl and KI) on the thickness, morphology, uniformity and degree of coverage of the grown  $MoS_2$  by using visible Raman spectroscopy and Scanning Electron Microscopy (SEM) as main characterization techniques.

#### **EDUCATION AND TRAINING**

#### **Master Degree**

**Politecnico di Milano** [ 01/03/2020 – 08/05/2023 ]

Address: Piazza Leonardo da Vinci, 32, 20133 Milan (Italy)

Website: www.polimi.it

Field(s) of study: Materials Engineering and Nanotechnology

Final grade: 108/110

Thesis: Effects of precursor chemistry in few-layers MoS2 from AP-CVD sulphurisation

#### **Bachelor Degree**

**Politecnico di Milano** [ 01/09/2015 – 05/03/2020 ]

Address: Piazza Leonardo da Vinci, 32, 20133 Milan (Italy)

Website: www.polimi.it

Field(s) of study: Materials Engineering and Nanotechnology

Final grade: 90/110

Thesis: Sintesi di rGO/SnO2 e formulazione di inchiostri per future applicazioni di sensoristica

#### Diploma di Liceo Scientifico Tradizionale

Liceo Scientifico Marie Curie [ 2010 - 2015 ]

Address: Via E. Cialdini, 181, Meda (Italy)

#### **PUBLICATIONS**

#### Impact of Cvd Chemistry on Band Alignment at the MoS2/SiO2 Interface

[2023]

Solid State Electronics (SSE)

P. P. Tummala, G. Delie, <u>A. Cataldo</u>, S. Ghomi, C. Martella, G. Ferrini, A. Molle, A. Lamperti, Valeri Afanas'ev

Reliable knowledge of energy alignment of electronic bands at interfaces of few layered Molybdenum Disulfide (MoS<sub>2</sub>) is crucial for designing MoS<sub>2</sub> based electronic devices. In this work, we have applied internal photoemission spectroscopy (IPE) to characterize this band alignment. MoS<sub>2</sub> films grown on SiO<sub>2</sub>(50nm)/Si using two different methods have been analyzed by IPE to determine the energy position of the semiconductor valence band (VB) relative to the reference level of the insulator conduction band (CB). We found that changing the MoS<sub>2</sub> growth method from Vapor Phase Reaction (VPR) of MoO<sub>3</sub> and sulfur, to Solid Precursor Film (SPF) of sulfurized AHM-NaOH spin coated MoS<sub>2</sub> film, results in significant ( $\approx$ 600 meV) enhancement in the electron barrier. Such effects are ascribed to the interaction of hydroxy groups from NaOH and AHM promoters with the SiO<sub>2</sub> surface leading to interface dipole modification.

#### **CONFERENCES AND SEMINARS**

# Role of precursors chemistry on the growth and band alignment of few-layers MoS2 from liquid chemical vapor deposition

[ Paestum (SA), 10/2023 ]

NMDC 2023 - Nanotechnology Materials and Devices Conference

P.P. Tummala, A. Cataldo, S. Ghomi, C. Massetti, C. Martella, G. Ferrini, A. Molle, V. Afanas'ev, A. Lamperti

## Impact of chemistry on the interface with substrate of MoS2 nanosheets grown by ambient pressure chemical vapor deposition

[ Napoli, 08/2023 ]

ICCGE 20 - International Conference on Crystal Growth and Epitaxy

A. Lamperti , P.P. Tummala, G. Delie, <u>A. Cataldo</u>, S. Ghomi, C.S. Casari , G. Ferrini, V. Afanas'ev, C. Martella, A. Molle

### Impact of Cvd Chemistry on Band Alignment at the MoS2/SiO2 Interface

[ Pizzo (VV), 06/2023 ]

INFOS 2023 - 23rd Conference on Insulating Films and Semiconductors

P. P. Tummala, G. Delie, A. Cataldo, S. Ghomi, C. Martella, G. Ferrini, A. Molle, A. Lamperti, Valeri Afanas'ev

#### **TECHNICAL SKILLS**

#### **Technical skills**

Advanced knowledge of **Office Package**, in particular **Word**, **Excel** and **PowerPoint**.

Technical software:

- •Origin, from handling of raw data to graph plots and data extrapolation.
- •Autodesk Inventor, skill acquired during an university course.
- ·Matlab, basic programming knowledge.

During my master thesis stage I learned to work with two **chemical vapour deposition machines (CVDs).** 

Regarding characterization techniques, I extensively worked on Raman Spectroscopy-